N584Hxxx Data Sheet

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1. General Description

N584Hxxx is a 4-bit microcontroller-based speech synthesizer with PWM mode output to drive the speaker directly. The synthesizer contains one voice-channel and/or dual tone melody. It has *Ultra I/OTM* to simplify the procedure of defining the output pattern, besides, it also includes 4-level Low Voltage Detection function. The N584Hxxx family contains several devices with different playback duration shown as below:

N584H	H009	H010	H019	H020	H029	H030	H039	H040
ROM (Kbit)	300	300	620	620	940	940	1260	1260
*Duration	12"	12"	24"	24"	37"	37"	49"	49"
I/O pins	4	8	4	8	4	8	4	8

N584H	H060	H070	H120	H170	H210	H260	H300
ROM (Kbit)	1740	1900	3340	4460	5740	7020	7980
*Duration	68"	74	131"	175"	225"	275"	312
I/O pins	8	8	16	16	16	16	16

Note1: The duration time is based on 4-bit NM4 at 6 KHz sampling rate

2. Features

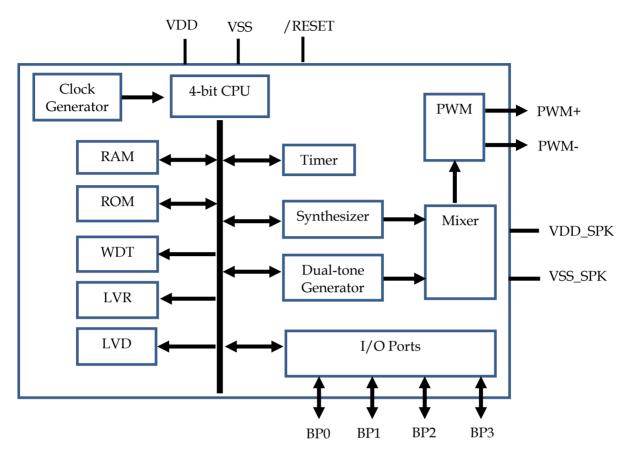
- Operating Voltage and CPU Frequency:
 - 1.8 ~ 5.5V (Fcpu = 4 MHz)
 - 2.0 ~ 5.5V (Fcpu = 8 MHz)
- Speech synthesis
 - 1-channel voice
 - Dual Tone Melody w/ 8 octaves (N584H120 ~ N584H300)
 - 4-bit NM4
- Build in internal oscillator (TRIM)
- Build in PWM Direct Drive circuit, with 4-level volume control
- Programmable sample rate
- Provides power management to save current consumption
 - 4 / 8 MHz system clock, with Ring type oscillator
 - STOP mode for stopping entire device's operation
- Provides 4 ~ 16 I/O

- N584H009, H019, H029, H039: 4 I/O (BP0)
- N584H010, H020, H030, H040, H060, H070: 8 I/O (BP0, BP1)
- N584H120, H170, H210, H260, H300: 16 I/O (BP0, BP1, BP2, BP3)
- High sink current capability
- Support capture timer to implement up to 8 capture sensor key
- Input can be set as active low (internal pull high) or active high (internal pull low)
- Provides 96*4 ~ 224*4 bits RAM
- Provides 64K*10 of program data
- Provides IR carrier generator (38 KHz or 56 KHz)
- Provides Watch Dog Timer (WDT)
- Provides Low Voltage Reset (LVR: 1.7V, 1.9V)
- Provides Low Voltage Detection (LVD: 2.2V, 2.4V, 3.0V, 3.3V) with deviation +/-5%
- Shared ROM for voice and program storage
- Supports *PowerScriptTM* for developing codes easily
- Full-fledged development system
 - Source-level ICE debugger (*PowerScriptTM* format)
 - Event synchronization mechanism
 - User-friendly GUI environment
 - It has *Ultra I/O^{TM}* to simplify the defined output pattern

3. Pad Description

Pad Name	I/O	Function
BP00~BP03	I/O	Bi-directional I/O port0, defined as input or output. As input, it can be set as pull-high, pull-low or floating. As output, it is defined as CMOS. BP03 can also be defined as IR carrier output (by mask option).
BP10~BP13	I/O	Bi-directional I/O port1, defined as input or output. As input, it can be set as pull-high, pull-low or floating. As output, it is defined as CMOS.
BP20~BP23	I/O	Bi-directional I/O port2, defined as input or output. As input, it can be set as pull-high, pull-low or floating. As output, it is defined as CMOS.
BP30~BP33	I/O	Bi-directional I/O port3, defined as input or output. As input, it can be set as pull-high, pull-low or floating. As output, it is defined as CMOS.
VDD, VDD_IO	-	Power supply
VSS, VSS_IO	-	Ground
PWM+	0	PWM drive positive output
PWM-	0	PWM drive negative output
VDD_SPK	-	Power supply for PWM drive
VSS_SPK	-	Ground for PWM drive
/RESET	Ι	Chip reset input with Schmitt trigger, internal pull-high

4. Block Diagram



5. Electrical Characteristics

5.1 Absolute Maximum Ratings

Item	Symbol	Conditions	Rated Value	Unit
Power Supply	VDD – VSS	-	-0.3 ~ +7.0	V
Input Voltage	VIN	All Inputs	VSS-0.3 ~ VDD+0.3	V
Storage Temp.	TSTG	-	-55 ~ +150	°C
Operating Temp.	TOPR	-	0 ~ +70	°C

NOTE:

Operating the device under conditions beyond those indicated above may cause permanent damage or affect device reliability.

5.2 DC Parameters

(VDD-VSS = 4.5V, VDD_SPK-VSS_SPK=4.5V, TA = 25° C; no load, unless otherwise specified)

Parameter	Sym	Conditions	Min	Тур	Max	Unit
Operating voltage	Vdd	Fcpu = 4 MHz Fcpu = 8 MHz	1.8 2.0		5.5 5.5	v
Quanting and	т	Fcpu=8 MHz, VDD=4.5V		1.5		
Operating current	I _{OP}	Fcpu=8 MHz, VDD=3.0V		1.0		mA
0, 11	т	VDD=4.5V			1	
Standby current	I_{SB}	VDD=3.0V			1	μA
Output high current	T	VDD=3.0V,Vout=2.6V	-4	-6		
(BP0, BP1, BP2, BP3)	I _{OH}	VDD=4.5V,Vout=2.6V		-30		mA
Output low current	T	VDD=3.0V,Vout=0.4V	8	12		A
(BP0, BP1, BP2, BP3)	I _{OL}	VDD=4.5V,Vout=1.0V		34		mA
PWM driver current	Ipw	R1=8Ω, connect to PWM+ and PWM-	200			mA
Pull-high resistor (BP0, BP1,BP2,BP3)	$R_{\rm PH}$	VDD=4.5V	90K 0.6M	150K 1M	210K 1.4M	Ω
Pull-low resistor (BP0, BP1,BP2,BP3)	R _{PL}	VDD=4.5V	90K 0.6M	150K 1M	210K 1.4M	Ω
		LVD_SEL[1:0] = 00	2.09	2.2	2.31	
LVD detect voltage	VLVD	$LVD_SEL[1:0] = 01$	2.28	2.4	2.52	v
2 · D deteet voluge	, , , , , , , ,	$LVD_SEL[1:0] = 10$	2.85	3.0	3.15	
		LVD_SEL[1:0] = 11	3.13	3.3	3.47	

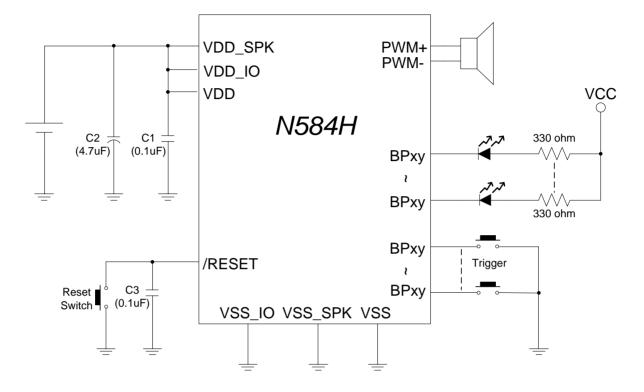
5.3 AC Parameters

(VDD-VSS = 4.5V, TA = 25° C; unless otherwise specified)

Parameter	Sym	Conditions	Min	Тур	Max	Unit
Main-clock Frequency	1-clock Frequency Fosc		7.95	8.19	8.44	MHz
Frequency deviation	$\frac{\Delta F}{F}$	$\frac{Fosc=8 \text{ MHz,}}{VDD=2.2 \sim 5.5V}$ $\frac{Fosc(max) - Fosc(min)}{Fosc(min)}$		3	5	%

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6. Typical Application Circuit



Notes:

- 1. In PCB layout, VSS_IO, VSS_SPK should be connected to VSS; and VDD_IO, VDD_SPK should be connected to VDD
- 2. The C1 capacitor 0.1uF is recommended to prevent the IC from hang-up as battery power bouncing. For power line layout in extended length, suggest C1 to be 1uF.
- 3. The C2 capacitor 4.7uF shunts between VDD and GND is for stabilized power noise
- 4. The C3 capacitor 0.1uF shunts between /Reset and GND is for power reset stability
- 5. BPxy means I/O pins. X: 0 ~ 3; Y: 0 ~ 3

7. Revision History

Version	Date	Substantial Changes	Page
A0.1	Mar. 2015	First establishment	
A0.2	Apr. 2015	Add part numbers	ALL
A0.3	May 2015	Add VDD range at Fcpu = 4 MHz	2, 5
A0.4	Jul. 2015	Revise note of AP circuit on C1 value	8
A1.0	Nov. 2015	Remove 'PRELIMINARY', update DC characteristic, Application circuit	1, 6, 8
A2.0	Jul. 2016	Revise application circuit	9

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